

COMPLEMENTARY SILICON POWER TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES

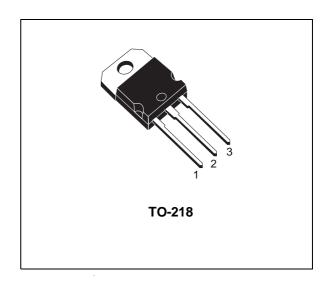
APPLICATIONS

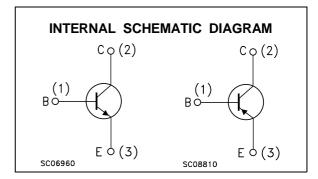
■ GENERAL PURPOSE SWITCHING

DESCRIPTION

The TIP33C is a silicon Epitaxial-Base NPN power transistor mounted in TO-218 plastic package. It is intented for use in linear and switching applications.

The complementary PNP type is TIP34C.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
		NPN	TIP33C	
		PNP	TIP34C	
V _{CBO}	Collector-Base Voltage (I _E = 0)		140	V
V _{CES}	Collector-Emitter Voltage (V _{BE} = 0)		140	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		100	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)		7	V
Ic	Collector Current		10	Α
I _{CM}	Collector Peak Current		12	Α
I_B	Base Current		3	Α
P _{tot}	Total Dissipation at T _c ≤ 25 °C		80	W
T _{stg}	Storage Temperature	•	-65 to 150	°C
Tj	Max. Operating Junction Temperature	•	150	°C

For PNP types voltage and current values are negative.

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THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.56	°C/W	
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ ^{o}C unless otherwise specified)

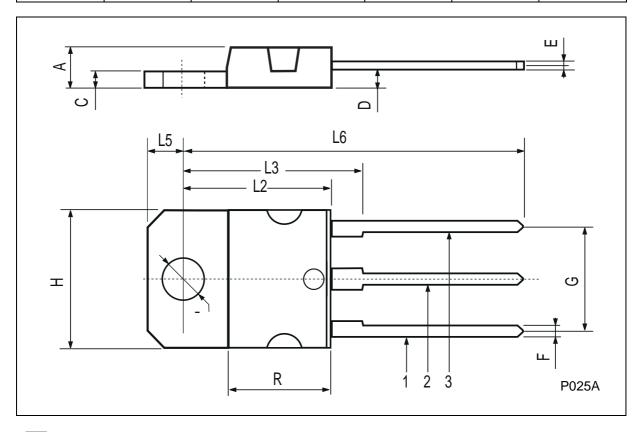
Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 140 V				400	μΑ
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 60 V				0.7	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V				1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA		100			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 3 A I _C = 10 A	$I_B = 0.3 A$ $I_B = 2.5 A$			1 4	V V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 3 A I _C = 10 A	$V_{CE} = 4 V$ $V_{CE} = 4 V$			1.6 3	V V
h _{FE} *	DC Current Gain	I _C = 1 A I _C = 3 A	V _{CE} = 4 V V _{CE} = 4 V	40 20		100	
h _{fe}	Small Signal Current Gain	I _C = 0.5 A f = 1 KHz	V _{CE} = 10 V	20			
f _T	Transition frequency	I _C = 0.5 A f = 1 MHz	V _{CE} = 10 V	3			MHz
t _{on} t _s t _f	RESISTIVE LOAD Turn-on Time Storage Time Fall Time	$VCC = 30V$ $V_{BB} = -6 V$ $t_p = 20 \mu s$	$I_C = 6 A$ $I_{B1} = -I_{B2} = 0.6 A$		0.6 0.4 1		μs μs μs

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

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TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.7		4.9	0.185		0.193	
С	1.17		1.37	0.046		0.054	
D		2.5			0.098		
Е	0.5		0.78	0.019		0.030	
F	1.1		1.3	0.043		0.051	
G	10.8		11.1	0.425		0.437	
Н	14.7		15.2	0.578		0.598	
L2	_		16.2	-		0.637	
L3		18			0.708		
L5	3.95		4.15	0.155		0.163	
L6		31			1.220		
R	_		12.2	-		0.480	
Ø	4		4.1	0.157		0.161	



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